

## FB23N20D-VB Datasheet

### N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
200	0.058at V <sub>GS</sub> = 10 V	35

#### FEATURES

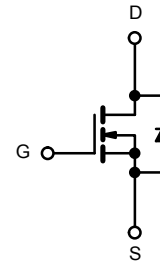
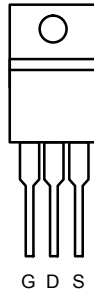
- TrenchFET<sup>®</sup> Power MOSFETS
- 175 °C Junction Temperature
- New Low Thermal Resistance Package
- Compliant to RoHS Directive 2002/95/EC



#### APPLICATIONS

- Industrial

TO-220AB



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	200	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 175 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	35
		T <sub>C</sub> = 125 °C	23
Pulsed Drain Current	I <sub>DM</sub>	70	A
Avalanche Current	I <sub>AR</sub>	35	
Repetitive Avalanche Energy <sup>a</sup>	E <sub>AR</sub>	61	mJ
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>C</sub> = 25 °C	300 <sup>b</sup>
		T <sub>A</sub> = 25 °C <sup>c</sup>	3.75
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.5	

Notes:

- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

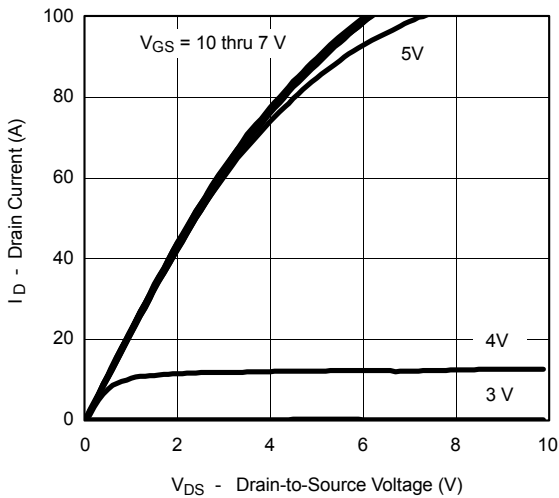
<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	200			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 30\text{ V}$			$\pm 250$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	70			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.058		$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.130		
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.170		
		$V_{GS} = 6\text{ V}, I_D = 15\text{ A}$		0.070		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		70		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2690		$\mu\text{F}$
Output Capacitance	$C_{oss}$			200		
Reverse Transfer Capacitance	$C_{rss}$			110		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 45\text{ A}$		95	140	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			28		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			34		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.6		$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 2.78\text{ }\Omega$ $I_D \equiv 45\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		22	35	ns
Rise Time <sup>c</sup>	$t_r$			220	330	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			40	60	
Fall Time <sup>c</sup>	$t_f$			145	220	
<b>Source-Drain Diode Ratings and Characteristics</b> ( $T_C = 25\text{ }^\circ\text{C}$ ) <sup>b</sup>						
Continuous Current	$I_S$				45	A
Pulsed Current	$I_{SM}$				70	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 45\text{ A}, V_{GS} = 0\text{ V}$		1	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 45\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		150	225	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			12	18	A
Reverse Recovery Charge	$Q_{rr}$			0.9	2	$\mu\text{C}$

Notes:

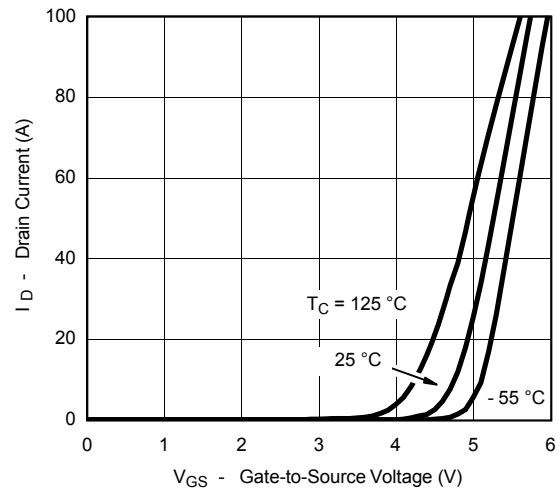
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

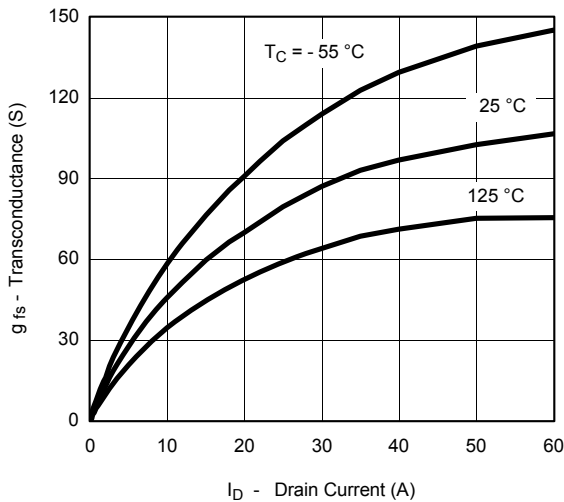
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



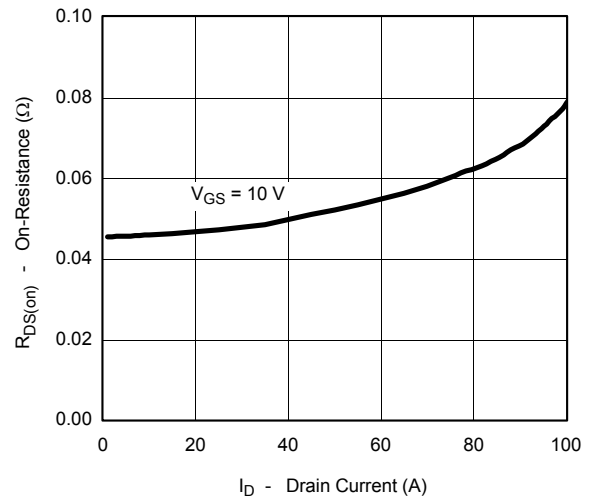
**Output Characteristics**



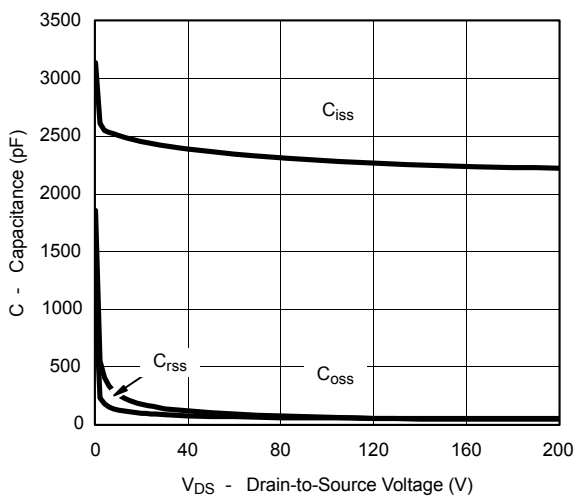
**Transfer Characteristics**



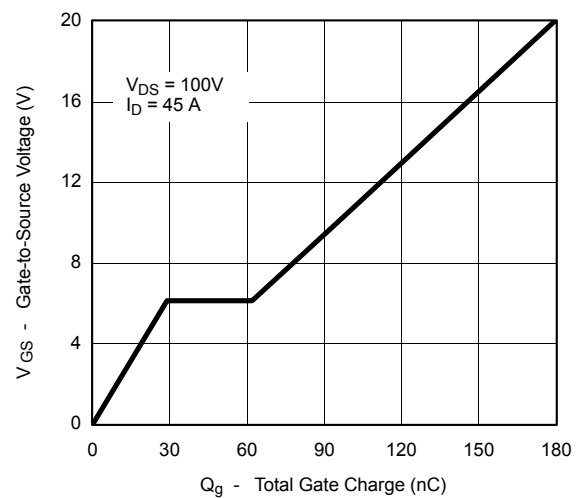
**Transconductance**



**On-Resistance vs. Drain Current**



**Capacitance**

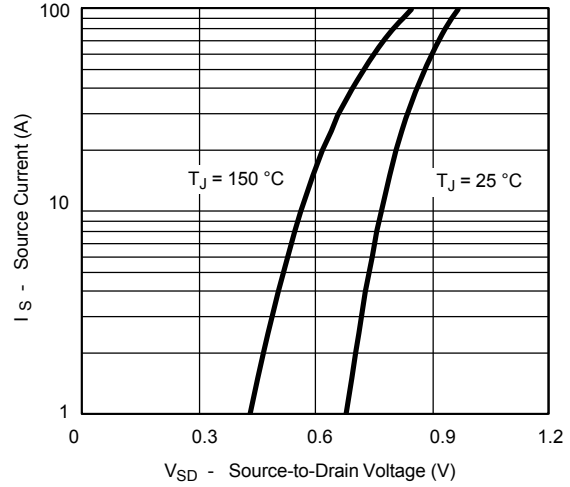


**Gate Charge**

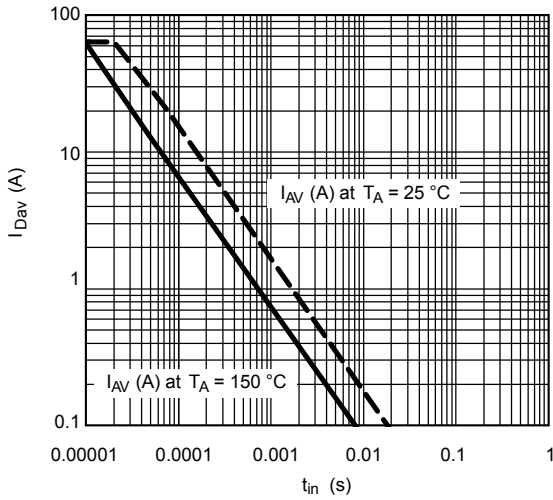
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



**Avalanche Current vs. Time**

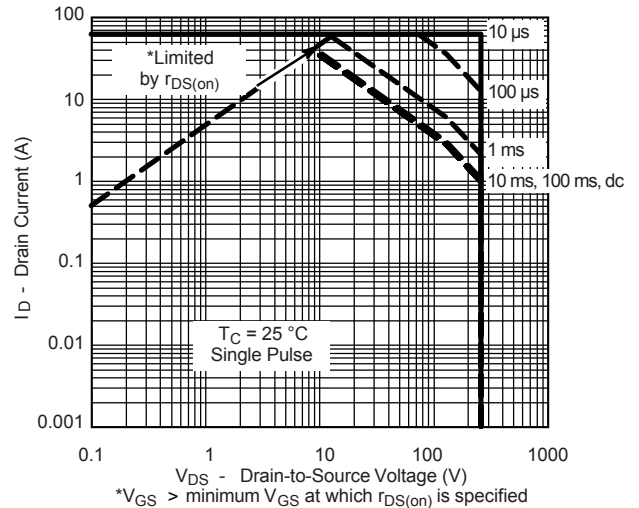


**Drain Source Breakdown vs. Junction Temperature**

**THERMAL RATINGS**



**Maximum Avalanche and Drain Current vs. Case Temperature**

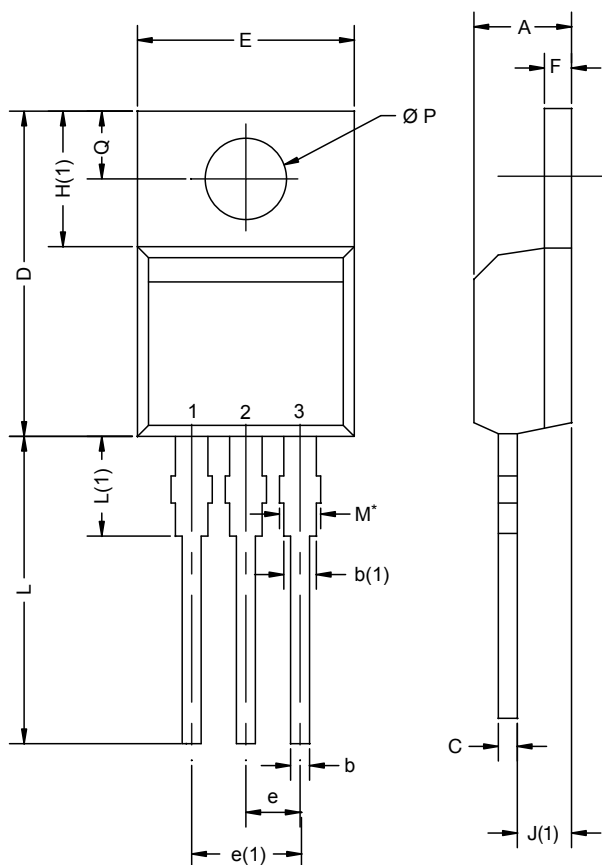


**Safe Operating Area, Case Temperature**



**Normalized Thermal Transient Impedance, Junction-to-Case**

### TO-220AB

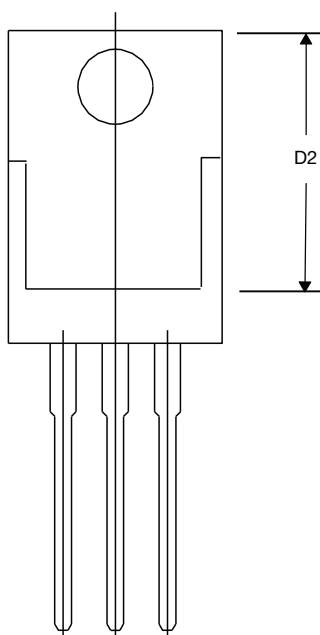


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T14-0413-Rev. P, 16-Jun-14  
DWG: 5471

**Note**

\* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM



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